

## Reliability of GaAs Discrete FETs

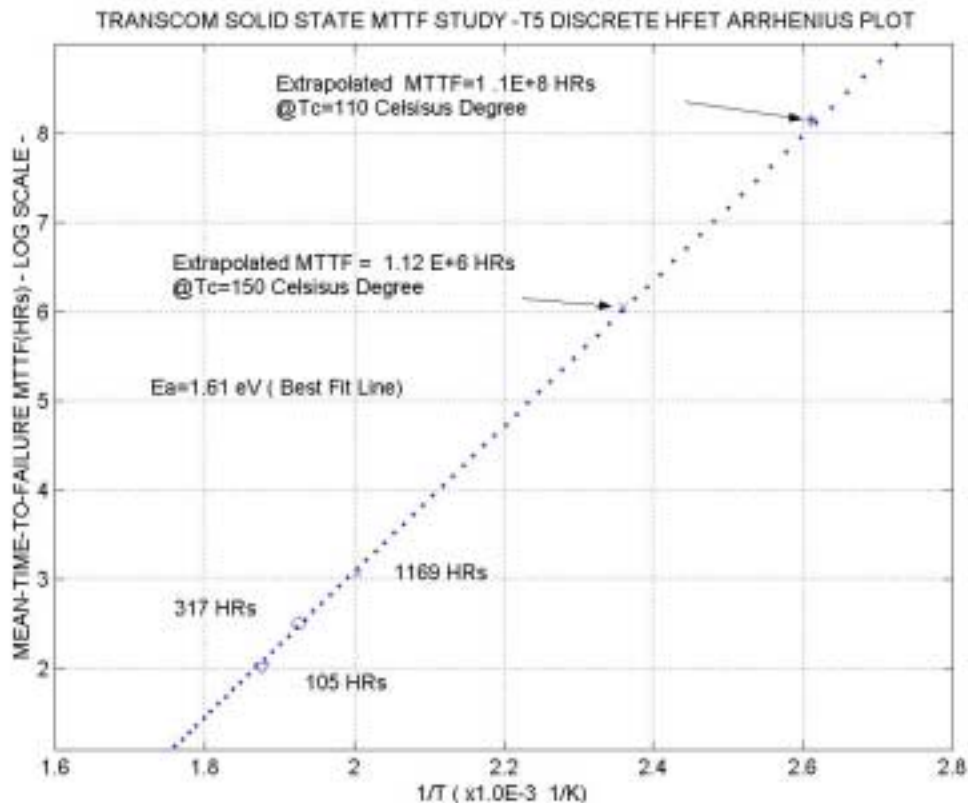


Figure 1

Figure 1 demonstrates the high temperature DC life test results of Transcom T5 (2.4 mm) GaAs HFET. The devices exhibit an extrapolated DC lifetime of more than  $10^8$  hours at 110 °C Channel Temperature. The MTTF test results derived from three elevated channel temperatures of 226 °C, 246 °C and 260 °C. Failure of the devices defined as 20 % degradation in  $I_{dss}$  from room temperature values.